

## Silicon NPN Power Transistors

## 2N6282 2N6283 2N6284

## DESCRIPTION

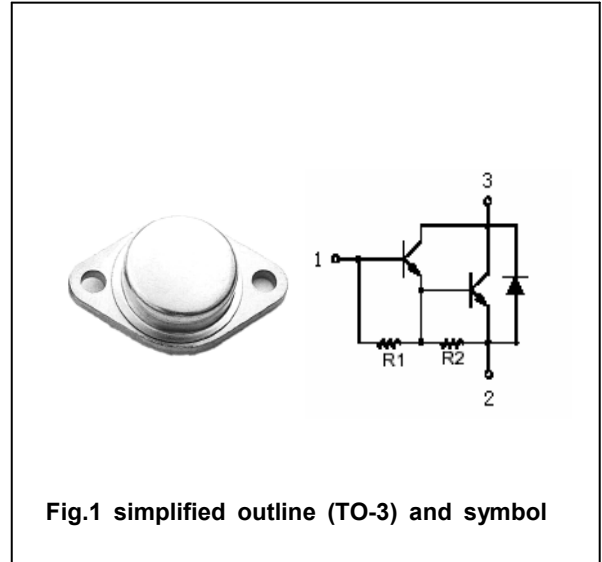
- With TO-3 package
- Complement to type 2N6285/6286/6287
- High DC current gain
- DARLINGTON

## APPLICATIONS

- For use in general-purpose amplifier and low-frequency switching applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a = \square$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2N6282	60	V
		2N6283	80	
		2N6284	100	
$V_{CEO}$	Collector-emitter voltage	2N6282	60	V
		2N6283	80	
		2N6284	100	
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		20	A
$I_{CM}$	Collector current-peak		40	A
$I_B$	Base current		0.5	A
$P_D$	Total Power Dissipation	$T_C = 25 \square$	160	W
$T_j$	Junction temperature		200	$\square$
$T_{stg}$	Storage temperature		-65~200	$\square$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.09	$\square/W$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	2N6282	I <sub>C</sub> =0.2A ; I <sub>B</sub> =0			V
		2N6283				
		2N6284				
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =10A; I <sub>B</sub> =40mA			2.0	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =20A ; I <sub>B</sub> =200mA			3.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =20A ; I <sub>B</sub> =200mA			4.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =10A ; V <sub>CE</sub> =3V			2.8	V
I <sub>CEO</sub>	Collector cut-off current	2N6282			1.0	mA
		2N6283				
		2N6284				
I <sub>CEx</sub>	Collector cut-off current	2N6282			0.5 5.0	mA
		2N6283				
		2N6284				
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			2.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =10A ; V <sub>CE</sub> =3V	750		18000	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =20A ; V <sub>CE</sub> =3V	100			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz			400	pF

PACKAGE OUTLINE

